

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

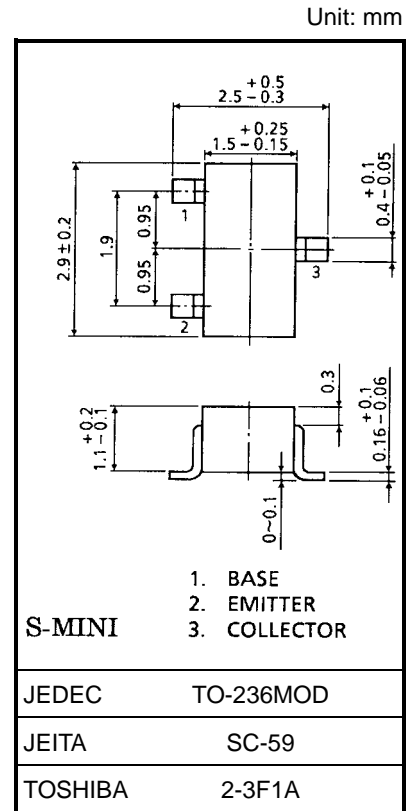
2SA1313

Audio Frequency Low Power Amplifier Applications
 Driver Stage Amplifier Applications
 Switching Applications

- Excellent hFE linearity: $h_{FE} (2) = 25$ (min)
 at $V_{CE} = -6$ V, $I_C = -400$ mA
- High voltage: $V_{CEO} = -50$ V (min)
- Complementary to 2SC3325
- Small package

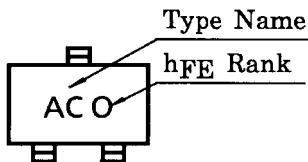
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-500	mA
Base current	I_B	-50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$



Weight: 0.012 g (typ.)

Marking

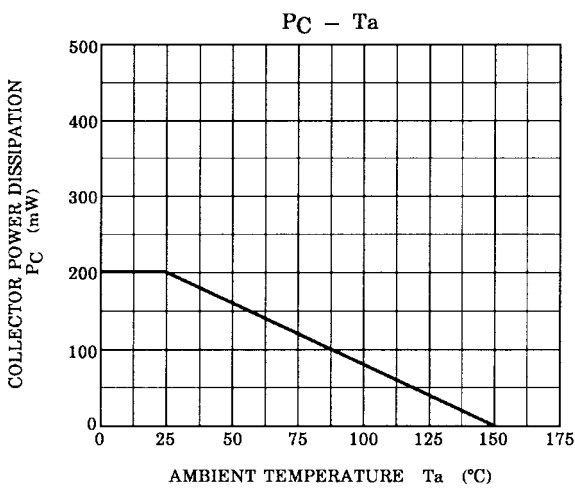
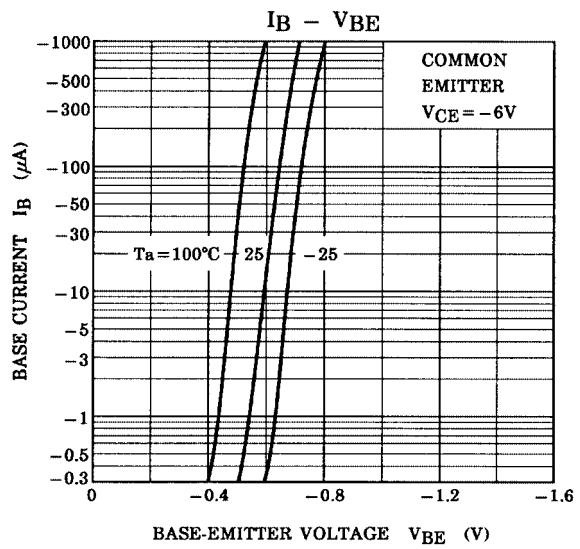
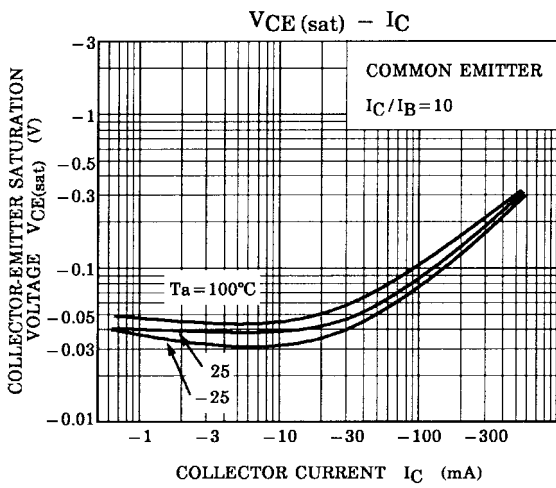
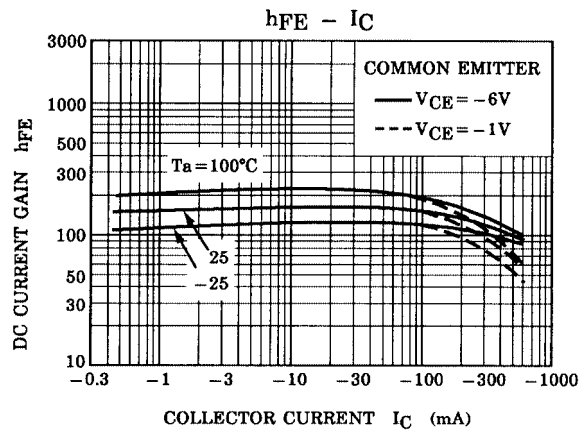
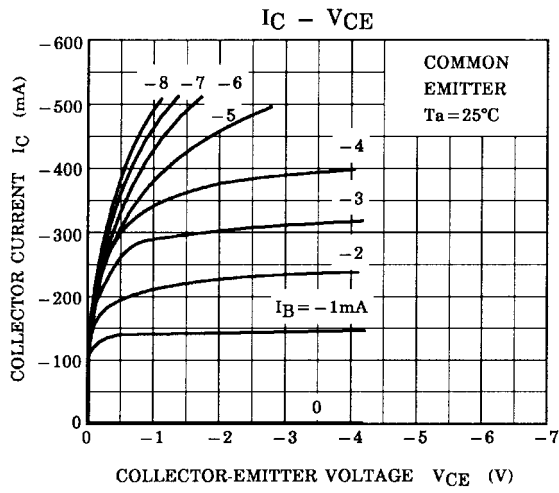


Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	μA
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	70	—	240	
	$h_{FE(2)}$ (Note)	$V_{CE} = -6\text{ V}, I_C = -400\text{ mA}$	25	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{ mA}, I_B = -10\text{ mA}$	—	-0.1	-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	—	-0.8	-1.0	V
Transition frequency	f_T	$V_{CE} = -6\text{ V}, I_C = -20\text{ mA}$	—	200	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	13	—	pF

Note: $h_{FE(1)}$ classification O: 70~140, Y: 120~240

$h_{FE(2)}$ classification O: 25 (min), Y: 40 (min)



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